



TO-92MOD Plastic-Encapsulated Transistors

2SA966 TRANSISTOR (PNP)

FEATURE

Power dissipation

$$P_{CM}: 0.9 \quad W(T_{amb}=25^{\circ}C)$$

Collector current

$$I_{CM}: -1.5 \quad A$$

Collector-base voltage

$$V_{(BR)CBO}: -30 \quad V$$

Operating and storage junction temperature range

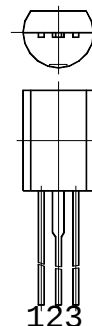
$$T_J, T_{stg}: -55^{\circ}C \text{ to } +150^{\circ}C$$

TO-92MOD

1. EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1mA, I_E = 0$	-30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1mA, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -30V, I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -2V, I_C = -500mA$	100	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1.5A, I_B = -0.03A$		-2	V
Base-emitter voltage	V_{BE}	$I_C = -500mA, V_{CE} = -2V$		-1	V
Transition frequency	f_T	$V_{CE} = -2V, I_C = -500mA$	100		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320